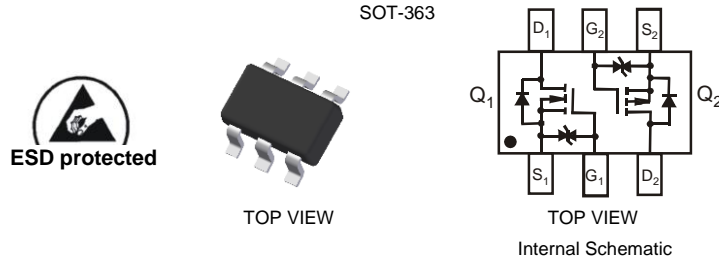


**COMPLEMENTARY PAIR ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**
**NEW PRODUCT**
**Features**

- Low On-Resistance
- Low Gate Threshold Voltage  $V_{GS(th)} < 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 2 & 3)**
- **Halogen and Antimony Free. "Green" Device (Note 4)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

**Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 7
- Ordering & Date Code Information: See Page 7
- Weight: 0.006 grams (approximate)


**Maximum Ratings N-CHANNEL – Q<sub>1</sub>** @ $T_A = 25^\circ C$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V
Drain Current (Note 1)	$I_D$	$T_A = 25^\circ C$	540
		$T_A = 85^\circ C$	390

**Maximum Ratings P-CHANNEL – Q<sub>2</sub>** @ $T_A = 25^\circ C$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V
Drain Current (Note 1)	$I_D$	$T_A = 25^\circ C$	-430
		$T_A = 85^\circ C$	-310

**Thermal Characteristics – Total Device** @ $T_A = 25^\circ C$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	$P_d$	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	$^\circ C/W$
Operating and Storage Temperature Range	$T_j, T_{STG}$	-65 to +150	$^\circ C$

- Notes:
1. Device mounted on FR-4 PCB.
  2. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  3. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  4. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

**Electrical Characteristics N-CHANNEL – Q<sub>1</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

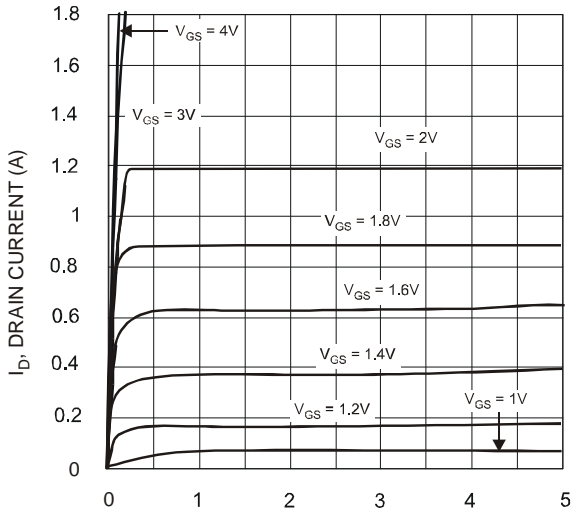
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	± 1	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.4	0.55	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 540mA
		—	0.5	0.70		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 500mA
		—	0.7	0.90		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 350mA
Forward Transfer Admittance	Y <sub>fs</sub>	200	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage (Note 5)	V <sub>SD</sub>	0.5	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	—	150	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	20	pF	

**Electrical Characteristics P-CHANNEL – Q<sub>2</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

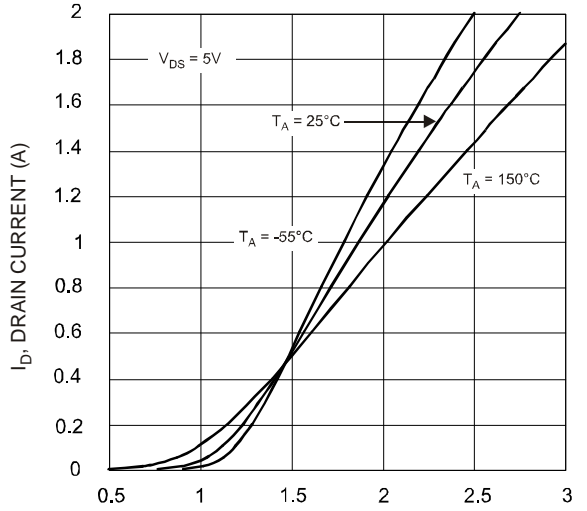
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	± 1.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.7	0.9	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA
		—	1.1	1.4		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
		—	1.7	2.0		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
Forward Transfer Admittance	Y <sub>fs</sub>	200	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage (Note 5)	V <sub>SD</sub>	-0.5	—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -115mA
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	—	175	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	30	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	20	pF	

Notes: 5. Short duration pulse test used to minimize self-heating effect.

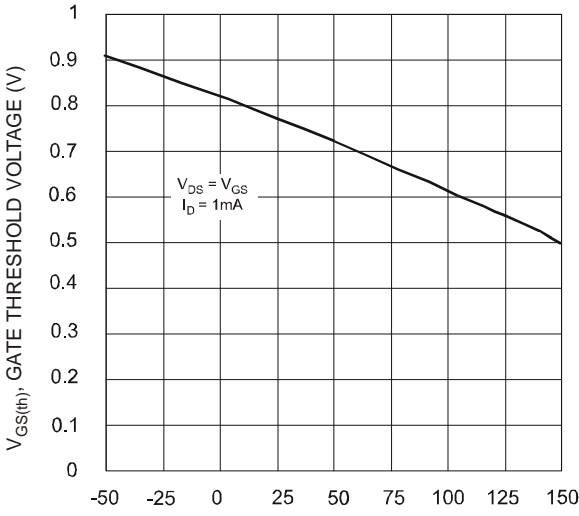
**Q<sub>1</sub>, N-CHANNEL**



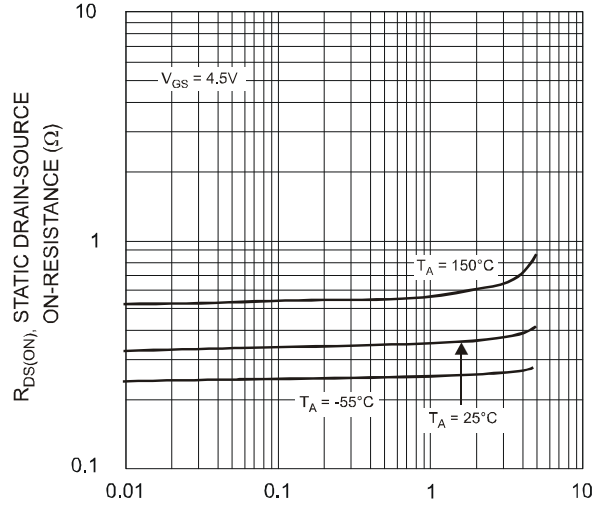
$V_{DS}$ , DRAIN SOURCE VOLTAGE (V)  
Fig. 1 Typical Output Characteristics



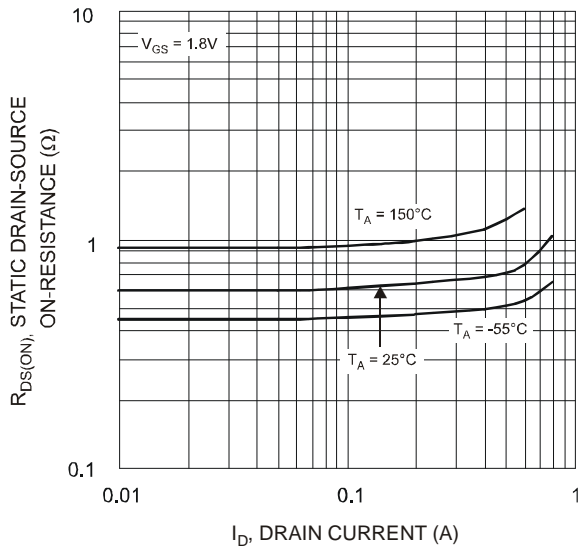
$V_{GS}$ , GATE SOURCE VOLTAGE (V)  
Fig. 2 Typical Transfer Characteristics



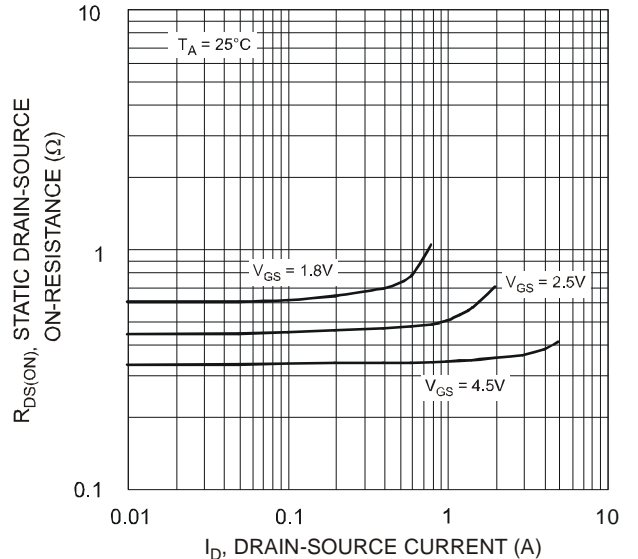
$T_A$ , AMBIENT TEMPERATURE (°C)  
Fig. 3 Gate Threshold Voltage vs. Ambient Temperature



$I_D$ , DRAIN CURRENT (A)  
Fig. 4 Static Drain-Source On-Resistance vs. Drain Current



$I_D$ , DRAIN CURRENT (A)  
Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



$I_D$ , DRAIN-SOURCE CURRENT (A)  
Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

**Q<sub>1</sub>, N-CHANNEL** (continued)

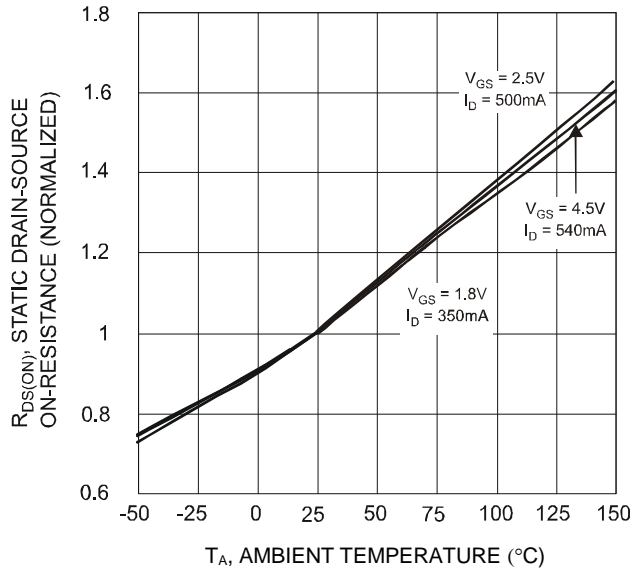


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

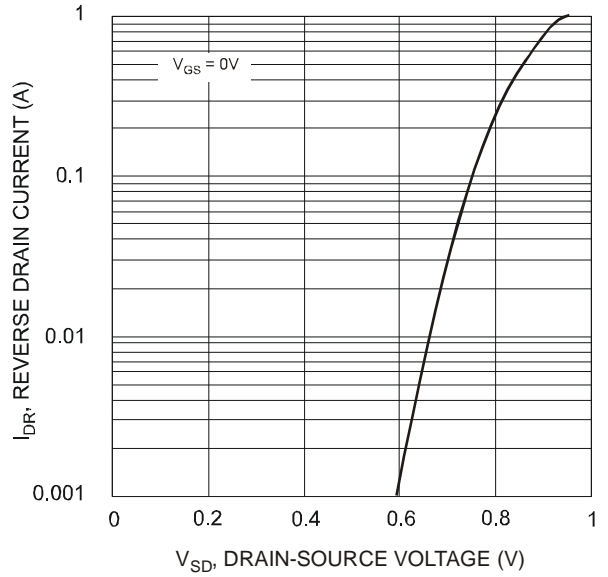


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

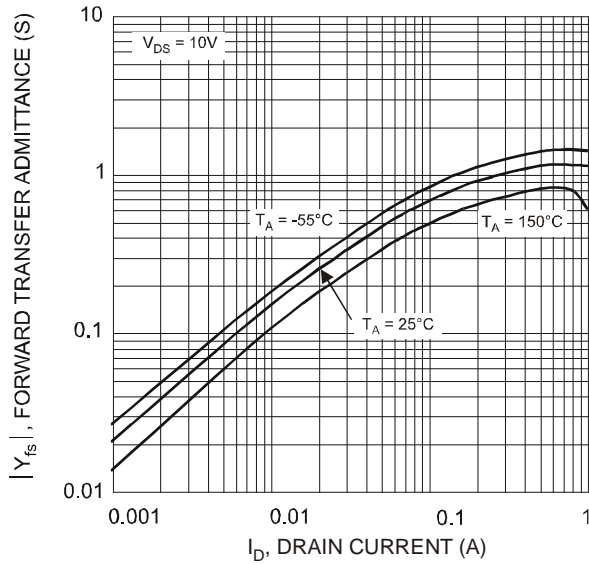


Fig. 9 Forward Transfer Admittance vs. Drain Current

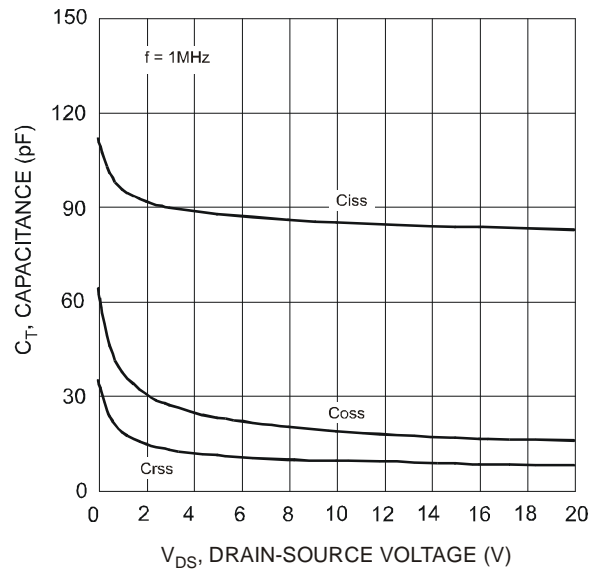


Fig. 10 Typical Capacitance

**Q<sub>2</sub>, P-CHANNEL**

NEW PRODUCT

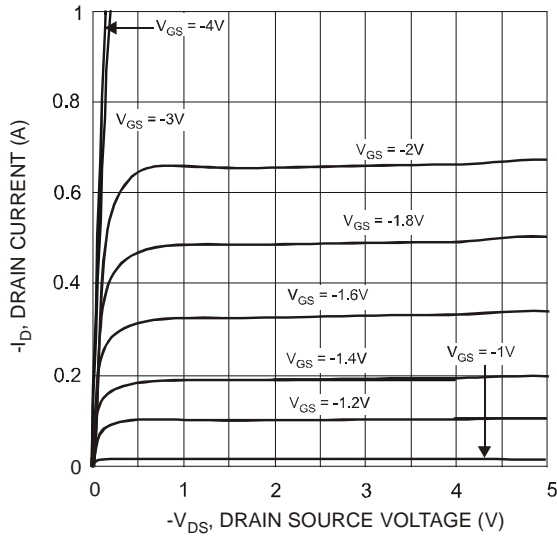


Fig. 11 Typical Output Characteristics

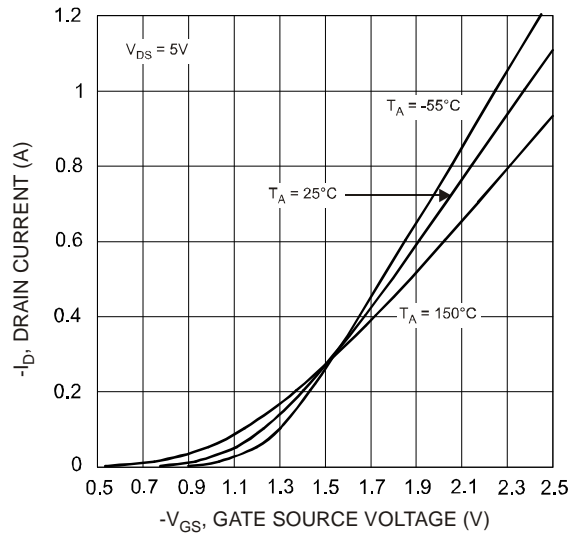


Fig. 12 Typical Transfer Characteristics

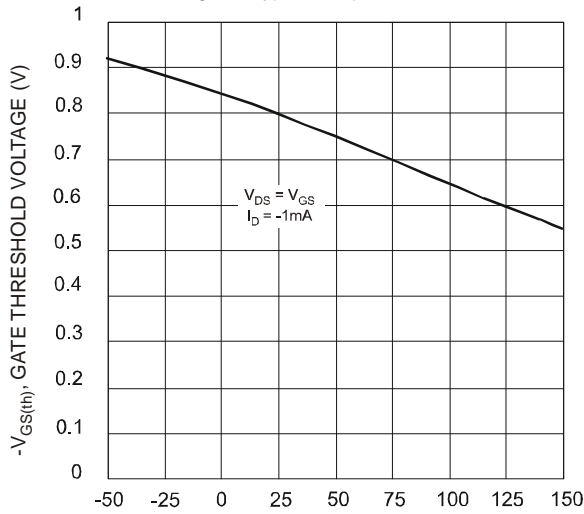


Fig. 13 Gate Threshold Voltage vs. Ambient Temperature

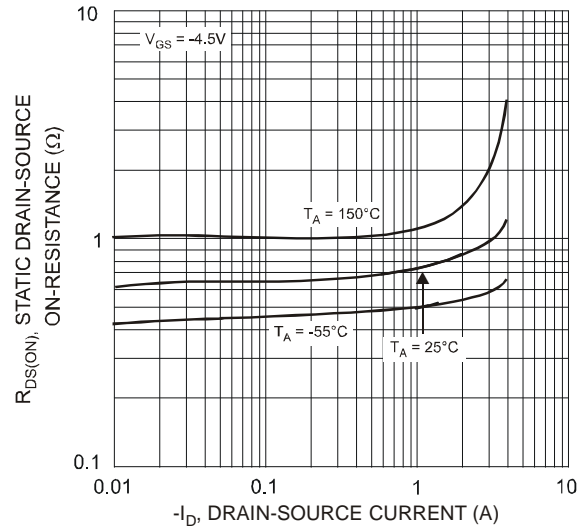


Fig. 14 Static Drain-Source On-Resistance vs. Drain Current

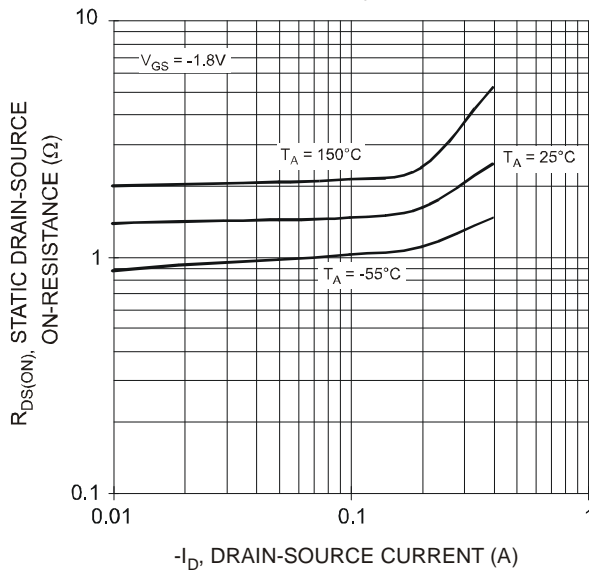


Fig. 15 Static Drain-Source On-Resistance vs. Drain Current

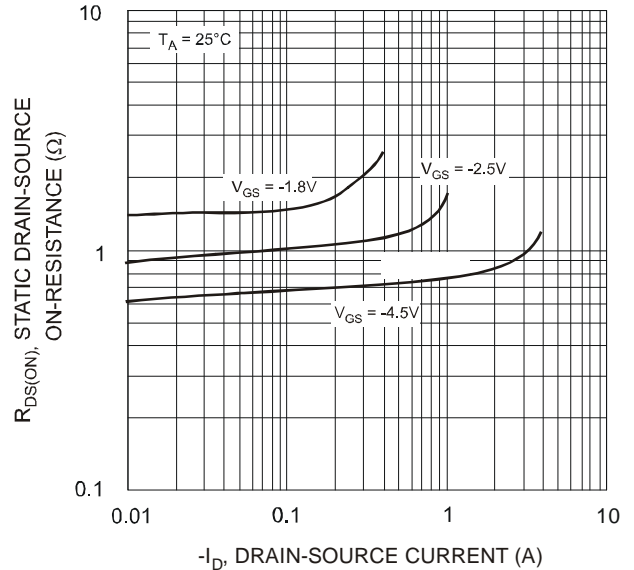


Fig. 16 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

**Q<sub>2</sub> P-CHANNEL** (continued)

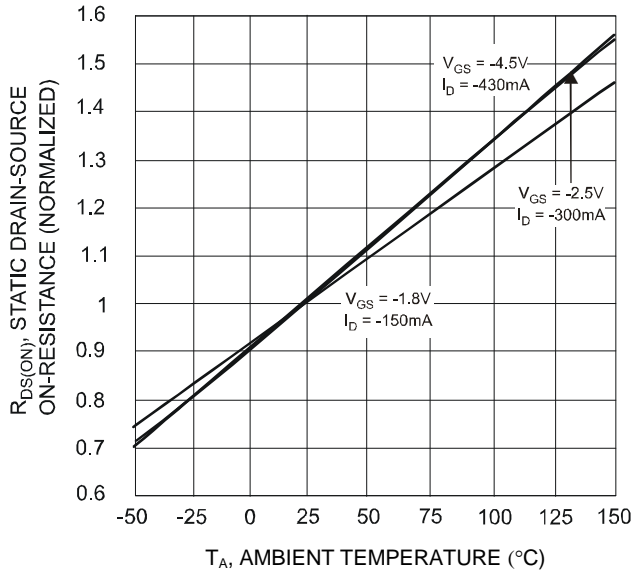


Fig. 17 Static Drain-Source On-State Resistance vs. Ambient Temperature

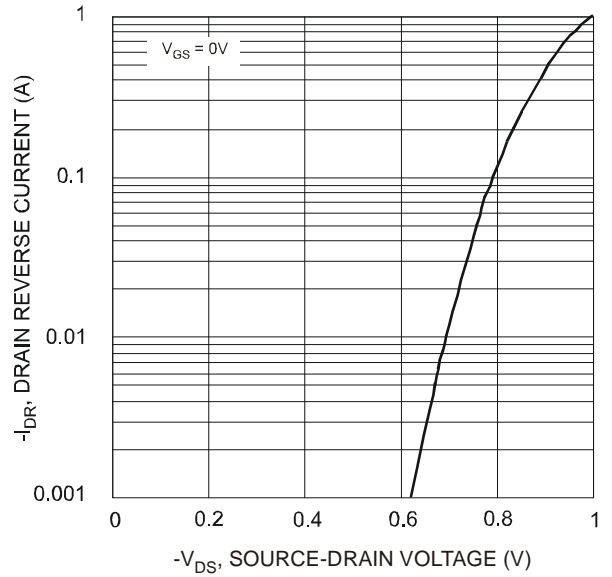


Fig. 18 Reverse Drain Current vs. Source-Drain Voltage

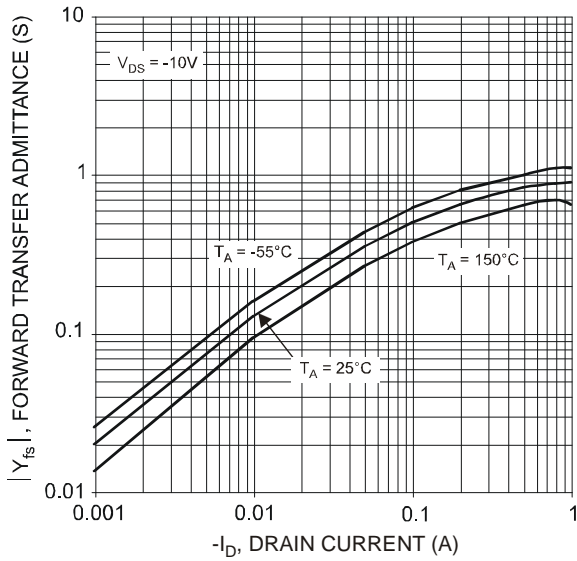


Fig. 19 Forward Transfer Admittance vs. Drain Current

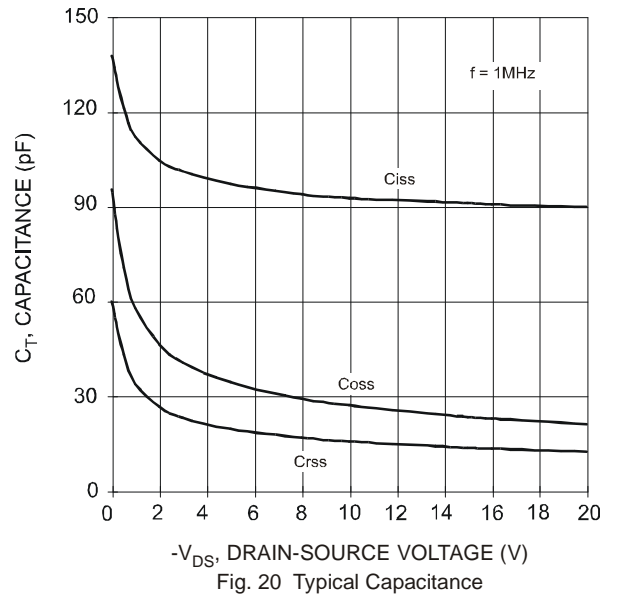


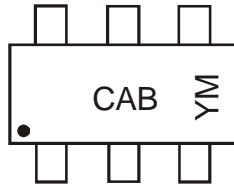
Fig. 20 Typical Capacitance

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DMC2004DWK-7	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



CAB = Marking Code  
 YM = Date Code Marking  
 Y = Year ex: U = 2007  
 M = Month ex: 9 = September

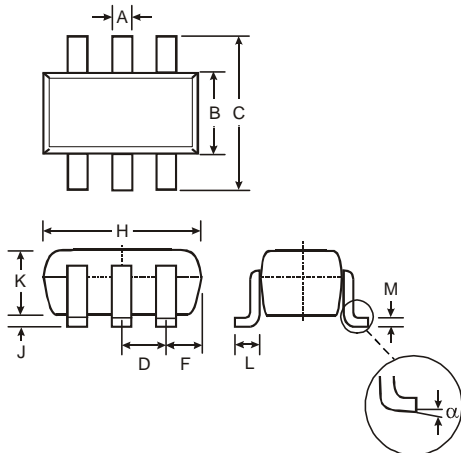
Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**

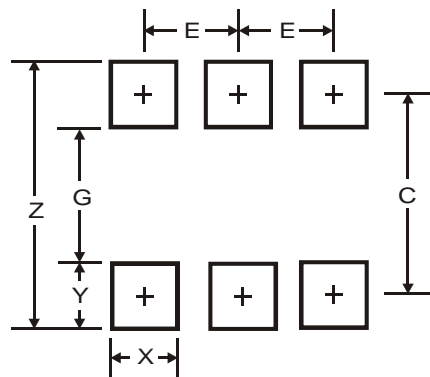
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
$\alpha$	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65

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1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

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